

1N5829 thru 1N5831

Features

- Metal of silicon rectifier, majority carrier conductor
- Guard ring for transient protection
- Low power loss high efficiency
- High surge capacity, High current capability

Maximum Ratings

- Operating Temperature: -65°C to +150°C
- Storage Temperature: -65°C to +150°C

MCC Part Number	Maximum Recurrent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
1N5829	20V	14V	20V
1N5830	25V	17.5V	25V
1N5831	35V	24.5V	35V

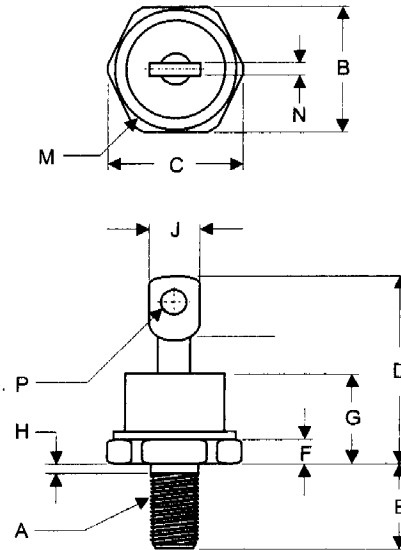
25 Amp Schottky Barrier Rectifier 20 to 35 Volts

Electrical Characteristics @ 25°C Unless Otherwise Specified

Average Forward Current	$I_{F(AV)}$	25 A	$T_L = 85^\circ\text{C}$
Peak Forward Surge Current	I_{FSM}	800A	8.3ms, half sine
Maximum Instantaneous Forward Voltage	V_F		$I_{FM} = 25 \text{ A};$ $T_A = 125^\circ\text{C}$
		.44V	
		.46V	
		.48V	
Maximum DC Reverse Current At Rated DC Blocking Voltage	I_R	20mA	$T_A = 25^\circ\text{C}$

*Pulse Test: Pulse Width 300µsec, Duty Cycle 1%

DO-4



A	10-32 UNF3A	Threads	Standard	Polarity
B	.424	.437	10.77	11.10
C	----	.505	----	12.82
D	.600	.800	15.24	20.32
E	.422	.453	10.72	11.50
F	.075	.175	1.91	4.44
G	----	.405	----	10.29
H	.163	.189	4.15	4.80
J	----	.310	----	7.87
M	----	.350	----	8.89
N	.020	.065	0.61	1.65
P	.060	.100	1.53	2.54

